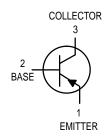
# **General Purpose Transistors PNP Silicon**



#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	40	Vdc
Collector-Base Voltage	V <sub>СВО</sub>	40	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current — Continuous	IC	200	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Power Dissipation @ T <sub>A</sub> = 60°C	PD	250	mW
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

#### THERMAL CHARACTERISTICS(1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	•
Collector-Emitter Breakdown Voltage (2) (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V(BR)CEO	40	_	Vdc
Collector-Base Breakdown Voltage (IC = 10 $\mu$ Adc, IE = 0)	V(BR)CBO	40	_	Vdc
Emitter-Base Breakdown Voltage (IE = 10 $\mu$ Adc, IC = 0)	V(BR)EBO	5.0	_	Vdc
Base Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>BL</sub>	_	50	nAdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	ICEX	_	50	nAdc

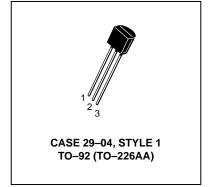
- 1. Indicates Data in addition to JEDEC Requirements.
- 2. Pulse Test: Pulse Width  $\leq$  300  $\mu s;$  Duty Cycle  $\leq$  2.0%.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 2

## 2N3905 2N3906\*

\*Motorola Preferred Device



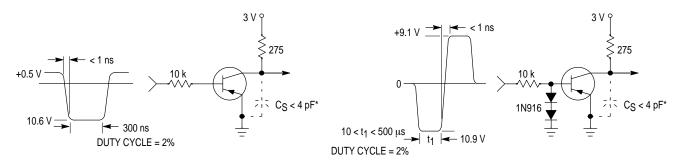


#### 2N3905 2N3906

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted) (Continued)

	Characteristic		Symbol	Min	Max	Unit
ON CHARACTERI	STICS(1)					
DC Current Gain (I <sub>C</sub> = 0.1 mAdc, V <sub>C</sub>	CE = 1.0 Vdc)	2N3905 2N3906	h <sub>FE</sub>	30 60	=	_
$(I_C = 1.0 \text{ mAdc}, V_C)$	CE = 1.0 Vdc)	2N3905 2N3906		40 80	_	
$(I_C = 10 \text{ mAdc}, V_C)$	<sub>CE</sub> = 1.0 Vdc)	2N3905 2N3906		50 100	150 300	
$(I_C = 50 \text{ mAdc}, V_C)$	<sub>CE</sub> = 1.0 Vdc)	2N3905 2N3906		30 60	_ _	
$(I_C = 100 \text{ mAdc}, V)$	'CE = 1.0 Vdc)	2N3905 2N3906		15 30	_	
Collector-Emitter Sa (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> (I <sub>C</sub> = 50 mAdc, I <sub>B</sub>	= 1.0 mAdc)		VCE(sat)		0.25 0.4	Vdc
Base-Emitter Satura (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> (I <sub>C</sub> = 50 mAdc, I <sub>B</sub>	= 1.0 mAdc)		VBE(sat)	0.65 —	0.85 0.95	Vdc
SMALL-SIGNAL (	CHARACTERISTICS				•	
Current-Gain — Bai (I <sub>C</sub> = 10 mAdc, V <sub>C</sub>	ndwidth Product CE = 20 Vdc, f = 100 MHz)	2N3905 2N3906	fΤ	200 250		MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub>	<u>=</u> = 0, f = 1.0 MHz)		C <sub>obo</sub>	_	4.5	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub>	c = 0, f = 1.0 MHz)		C <sub>ibo</sub>	_	10.0	pF
Input Impedance (I <sub>C</sub> = 1.0 mAdc, V <sub>0</sub>	CE = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	h <sub>ie</sub>	0.5 2.0	8.0 12	kΩ
Voltage Feedback Ra (I <sub>C</sub> = 1.0 mAdc, V <sub>0</sub>	atio CE = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	h <sub>re</sub>	0.1 0.1	5.0 10	X 10 <sup>-4</sup>
Small–Signal Curren (I <sub>C</sub> = 1.0 mAdc, V <sub>0</sub>	nt Gain CE = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	h <sub>fe</sub>	50 100	200 400	_
Output Admittance (I <sub>C</sub> = 1.0 mAdc, V <sub>0</sub>	CE = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	h <sub>oe</sub>	1.0 3.0	40 60	μmhos
Noise Figure (I <sub>C</sub> = 100 μAdc, V <sub>C</sub>	CE = 5.0 Vdc, R <sub>S</sub> = 1.0 k Ω, f = 1.0 kHz)	2N3905 2N3906	NF		5.0 4.0	dB
SWITCHING CHAF	RACTERISTICS					
Delay Time	(V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = 0.5 Vdc,		t <sub>d</sub>	_	35	ns
Rise Time	I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 1.0 mAdc)		t <sub>r</sub>		35	ns
Storage Time	(Vac = 3.0 Vda   a = 40 mAda	2N3905 2N3906	t <sub>s</sub>	_	200 225	ns
Fall Time	- (V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mAd	2N3905 2N3906	t <sub>f</sub>	_	60 75	ns

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s; Duty Cycle  $\leq$  2.0%.

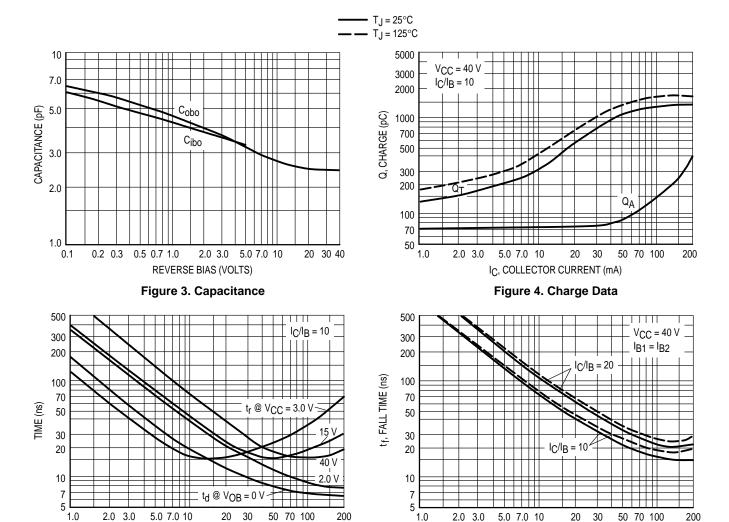


\* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

#### TYPICAL TRANSIENT CHARACTERISTICS



I<sub>C</sub>, COLLECTOR CURRENT (mA)

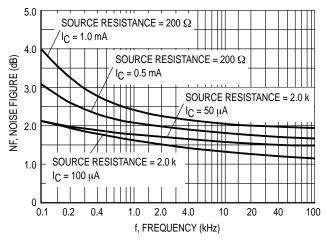
Figure 5. Turn-On Time

I<sub>C</sub>, COLLECTOR CURRENT (mA)

Figure 6. Fall Time

# TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = -5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth} = 1.0 \text{ Hz})$ 



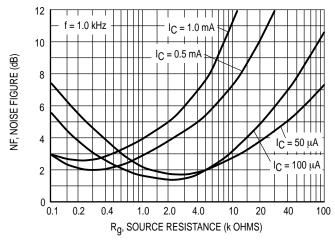
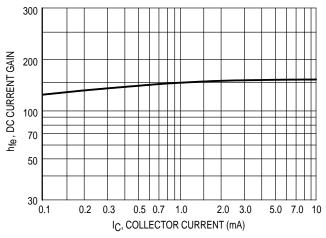


Figure 7.

Figure 8.

#### h PARAMETERS

 $(V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C})$ 



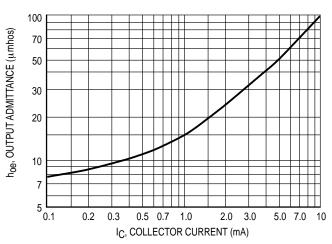


Figure 9. Current Gain

Figure 10. Output Admittance

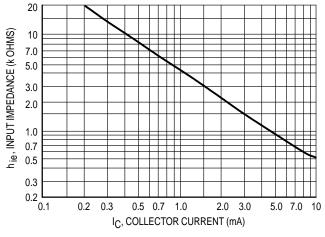




Figure 11. Input Impedance

Figure 12. Voltage Feedback Ratio

#### TYPICAL STATIC CHARACTERISTICS

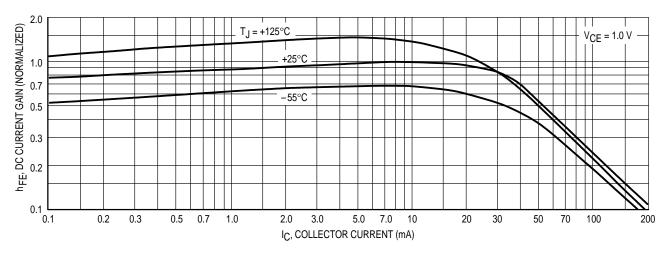


Figure 13. DC Current Gain

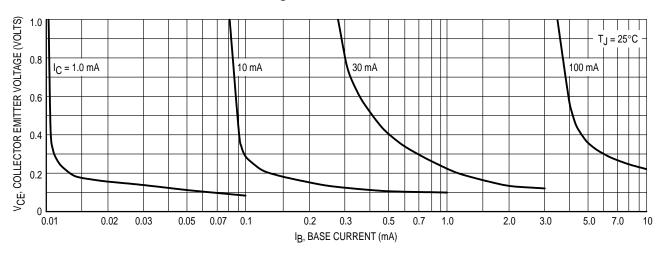


Figure 14. Collector Saturation Region

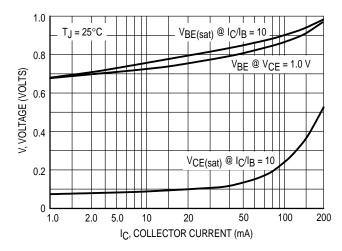
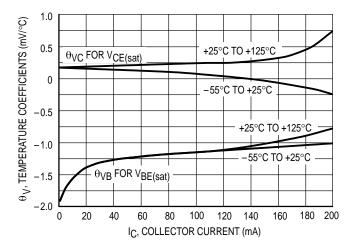
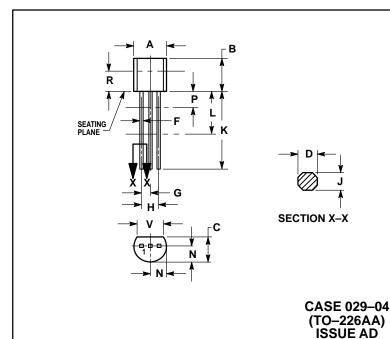


Figure 15. "ON" Voltages



**Figure 16. Temperature Coefficients** 

#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- Y14.5M, 1302.
  CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION P APPLIES BETWEEN P AND L.
  DIMENSION D AND J APPLY BETWEEN L AND K
  MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
ם	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Η	0.095	0.105	2.42	2.66
7	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 1:

PIN 1. EMITTER BASE 3. COLLECTOR

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